

Infrared Emitting Diodes(GaAs)

KODENSHI

EL - 325

The EL-325 is a GaAs IRED mounted in a low profile clear epoxy package. This IRED is both compact and easy to mount.

FEATURES

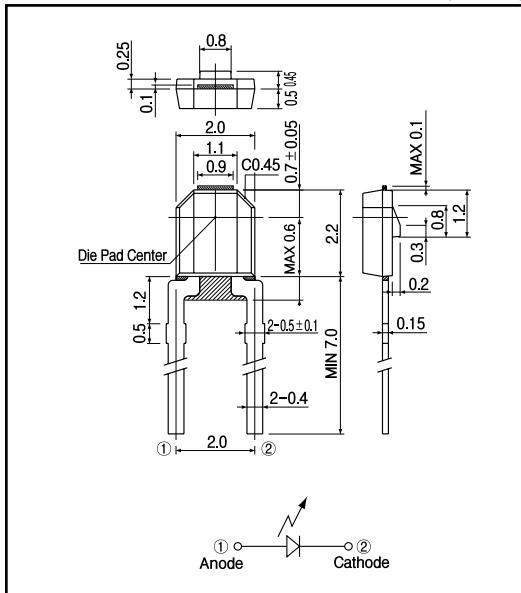
- Ultra compact
 - Low profile
 - Snap-in mount is possible

APPLICATIONS

- Photointerrupters
 - Optical equipment

DIMENSIONS

(Unit : mm)



MAXIMUM RATINGS

(Ta=25)

Item	Symbol	Rating	Unit
Reverse voltage	V_R	5	V
Forward current	I_F	50	mA
Power dissipation	P_D	100	mW
Pulse forward current ¹⁾	I_{FP}	0.5	A
Operating temp.	To pr.	- 25 + 85	
Storage temp.	T stg.	- 30 + 85	
Soldering temp. ²⁾	T sol.	260	

*1. pulse width : tw 100 sec.period : T = 10msec.

*2. For MAX.5 seconds at the position of 2 mm from the package

ELECTRO-OPTICAL CHARACTERISTICS

(Ta=25)

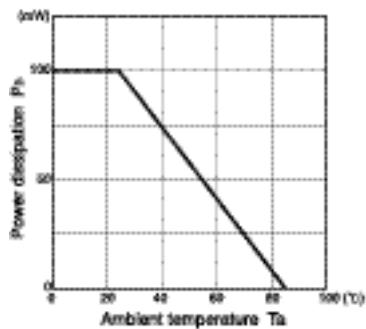
Item	Symbol	Conditions	Min.	Typ.	Max.	Unit.
Forward voltage	V_f	$I_f = 50\text{mA}$			1.6	V
Reverse current	I_r	$V_R = 5\text{V}$			10	μA
Peak emission wavelength	λ_p	$I_f = 50\text{mA}$		940		nm
Spectral bandwidth		$I_f = 50\text{mA}$		50		nm
Radiant intensity ⁻³	P_o	$I_f = 50\text{mA}$		0.7		mW/sr
Half angle				± 50		deg.

*3. Measured by tester of KODENSHI CORP.

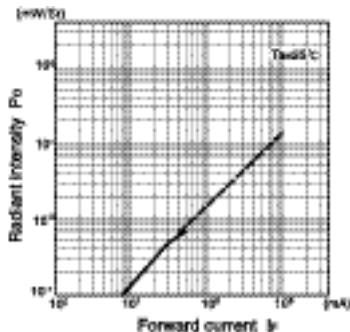
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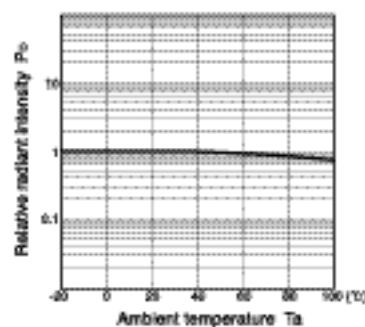
**Power dissipation Vs.
Ambient temperature**



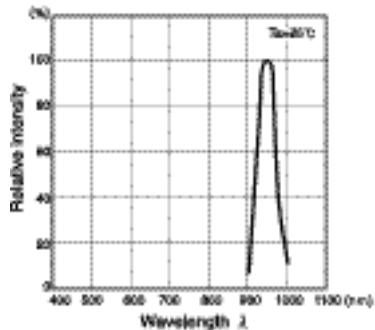
**Radiant intensity Vs.
Forward current**



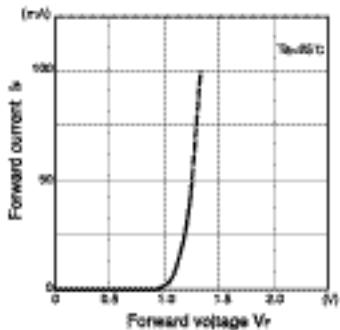
**Relative radiant intensity Vs.
Ambient temperature**



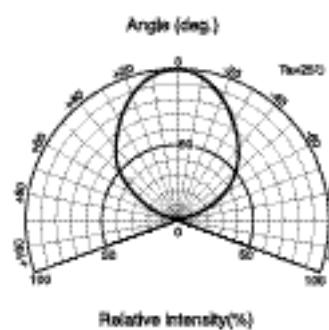
**Relative intensity Vs.
Wavelength**



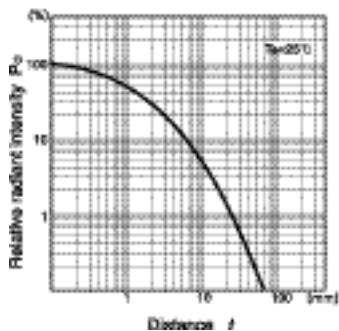
**Forward current vs.
Forward voltage**



Radiant Pattern



**Relative radiant intensity Vs.
Distance**



Relative radiant intensity Vs.
Distance test method

